

# Nobuhiko Mitoma

## List of Publications by Year in descending order

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24  
papers

691  
citations

686830

13  
h-index

610482

24  
g-index

24  
all docs

24  
docs citations

24  
times ranked

1079  
citing authors

#	ARTICLE	IF	CITATIONS
1	Perfluorocycloparaphenylenes. <i>Nature Communications</i> , 2022, 13, .	5.8	16
2	Gate-controlled photo-oxidation of graphene for electronic structure modification. <i>Journal of Materials Chemistry C</i> , 2019, 7, 1904-1912.	2.7	7
3	Hole-transporting materials based on thiophene-fused arenes from sulfur-mediated thienannulations. <i>Materials Chemistry Frontiers</i> , 2018, 2, 275-280.	3.2	16
4	Effect of carbon doping on threshold voltage and mobility of In-Si-O thin-film transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018, 36, 061206.	0.6	5
5	Carbon Nanosheets by Morphologyâ€Retained Carbonization of Twoâ€Dimensional Assembled Anisotropic Carbon Nanorings. <i>Angewandte Chemie - International Edition</i> , 2018, 57, 9679-9683.	7.2	80
6	Synthesis, properties, and crystal structures of Î€-extended double [6]helicenes: contorted multi-dimensional stacking lattice. <i>Organic and Biomolecular Chemistry</i> , 2017, 15, 4697-4703.	1.5	61
7	Correlation between active layer thickness and ambient gas stability in IGZO thin-film transistors. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 025102.	1.3	4
8	Phase transitions from semiconductive amorphous to conductive polycrystalline in indium silicon oxide thin films. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	13
9	Codoping of zinc and tungsten for practical high-performance amorphous indium-based oxide thin film transistors. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	23
10	Influence of Al <sub>2</sub> O <sub>3</sub> layer insertion on the electrical properties of Ga-In-Zn-O thin-film transistors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	0.9	6
11	Enhanced sensing response of oxidized graphene formed by UV irradiation in water. <i>Nanotechnology</i> , 2015, 26, 105701.	1.3	10
12	Dopant selection for control of charge carrier density and mobility in amorphous indium oxide thin-film transistors: Comparison between Si- and W-dopants. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	56
13	Suppression of excess oxygen for environmentally stable amorphous In-Si-O thin-film transistors. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	25
14	Reduction of the interfacial trap density of indium-oxide thin film transistors by incorporation of hafnium and annealing process. <i>AIP Advances</i> , 2015, 5, .	0.6	16
15	Stable amorphous In <sub>2</sub> O <sub>3</sub> -based thin-film transistors by incorporating SiO <sub>2</sub> to suppress oxygen vacancies. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	83
16	Low-temperature processable amorphous In-W-O thin-film transistors with high mobility and stability. <i>Applied Physics Letters</i> , 2014, 104, 152103.	1.5	79
17	Controllable film densification and interface flatness for high-performance amorphous indium oxide based thin film transistors. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	9
18	Spin injection and detection in a graphene lateral spin valve using an yttrium-oxide tunneling barrier. <i>Applied Physics Express</i> , 2014, 7, 085101.	1.1	6

#	ARTICLE	IF	CITATIONS
19	Self-formed copper oxide contact interlayer for high-performance oxide thin film transistors. Applied Physics Letters, 2014, 105, .	1.5	13
20	Photo-oxidation of Graphene in the Presence of Water. Journal of Physical Chemistry C, 2013, 117, 1453-1456.	1.5	45
21	Gate-controlled ultraviolet photo-etching of graphene edges. Applied Physics Letters, 2013, 103, .	1.5	12
22	Coexistence of Dirac-cone states and superconductivity in iron pnictide $\text{Ba}(\text{Fe}_{1-x}\text{Ru}_x\text{As})_2$ . Physical Review B, 2011, 84, .	1.1	27
23	Analysis of Degradation in Graphene-Based Spin Valves. Applied Physics Express, 2009, 2, 123004.	1.1	9
24	Robustness of Spin Polarization in Graphene-Based Spin Valves. Advanced Functional Materials, 2009, 19, 3711-3716.	7.8	70